Pushing Materials Research towards a commercial impact



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why study materials with femtosecond pulses?













Nontransparent materials



Nontransparent materials



Nontransparent materials

gap determines interaction



	ph	otoi	n en	ergy	/ < k	band	gap	\longrightarrow nonlinear interaction							





Outline

1/24/03

110

- transparent materials
- bulk micromachining
- non transparent materials

optical hyperdoping

high intensity at focus...



... causes nonlinear ionization...



and 'microexplosion' causes microscopic damage...





Some applications:

- data storage
- waveguides
- microfluidics



waveguide micromachining geometries



Dark-field scattering



block probe beam...



... bring in pump beam...



... damage scatters probe beam













vary numerical aperture





fit gives threshold intensity: $I_{th} = 2.5 \times 10^{17} \text{ W/m}^2$



vary material...


...threshold varies with band gap (but not much!)



would expect much more than a factor of 2



critical density reached by multiphoton for low gap only



avalanche ionization important at high gap



what prevents damage at low NA?

Competing nonlinear effects:

- multiphoton absorption
- supercontinuum generation
- self-focusing

why the difference?



very different confocal length/interaction length



high NA: interaction length too short for self-focusing

threshold for supercontinuum generation



threshold for damage



Points to keep in mind:

- threshold critically dependent on NA
- surprisingly little material dependence
- avalanche ionization important



Nature Photonics 2, 219 (2008)

Outline

1/24/03 9 kJ/m 9 kJ/m 11.0

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- transparent materials
- bulk micromachining
- non transparent materials
 - ptical hyperdoping

threshold decreases with increasing numerical aperture



less than 10 nJ at high numerical aperture!



amplified laser: 1 kHz, 1 mJ



heat diffusion time: $\tau_{diff} \approx 1 \ \mu s$

long cavity oscillator: 25 MHz, 25 nJ



heat diffusion time: $\tau_{diff} \approx 1 \ \mu s$



High repetition-rate micromachining:

- structural changes exceed focal volume
- spherical structures
- density change caused by melting





the longer the irradiation...



the longer the irradiation...



the longer the irradiation...



the longer the irradiation...



... the larger the radius



at high-rep rate: internal "point-source of heat"

waveguide micromachining



Opt. Lett. 26, 93 (2001)

waveguide micromachining





Opt. Lett. 26, 93 (2001)

structures guide light



Opt. Lett. 26, 93 (2001)

near-field profiles



Sagitta, Inc.

index profile at 2.5 mm/s





Sagitta, Inc.

index profile at 10 mm/s





Sagitta, Inc.

curved waveguides



curved waveguides



curved waveguides


curved waveguides



curved waveguides



photonic fabrication techniques

	fs micromachining	other
loss (dB/cm)	< 3	0.1–3
bending radius	36 mm	30–40 mm
Δn	2 x 10 ⁻³	10 ⁻⁴ – 0.5
3D integration	Y	N

photonic devices



all-optical sensor



all-optical sensor



all-optical sensor



all-optical sensor



all-optical sensor



all-optical sensor



all-optical sensor



all-optical sensor



Outline

1/24/03 9 kJ/m 9 kJ/m 11.0

- transparent materials
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irradiate with 100-fs 10 kJ/m² pulses



FUST



Introduction



Introduction

absorptance
$$(1 - R_{int} - T_{int})$$



absorptance
$$(1 - R_{int} - T_{int})$$



Introduction



absorptance
$$(1 - R_{int} - T_{int})$$



band structure changes: defects and/or impurities

substrate/dopant combinations

dopants:

N	0	F
Р	S	CI
	Se	
Sb	Те	

substrate/dopant combinations

dopants:



substrates:

- Si Ge ZnO InP GaAs
- Ti Ag Al Cu Pd Rh Ta Pt

























cross-sectional Transmission Electron Microscopy
M. Wall, F. Génin (LLNL)













- 300-nm disordered surface layer
- undisturbed crystalline core
- surface layer: nanocrystalline Si with 1.6% sulfur

μm

two processes: melting and ablation

relevant time scales



relevant time scales



different thresholds:

melting: 1.5 kJ/m²

ablation: 3.1 kJ/m²















ероху		
laser affected region		
substrate		
100 nm		







secondary ion mass spectrometry







Things to keep in mind

- rapid melting and resolidification causes doping
- ablation causes morphology changes
- about 1% impurity in 100-nm thick surface layer

Outline

11.0

213800

- transparent materials
- bulk micromachining
- non transparent materials

1/24/03 9 kJ/m 17 500

optical hyperdoping

absorptance
$$(1 - R_{int} - T_{int})$$



Asenbaum, Vienna

effect of annealing on IR absorptance



what dopant states/bands cause IR absorption?

1 part in 10⁶ sulfur introduces donor states in gap



Janzén et al., Phys. Rev. B 29, 1907 (1984)

1 part in 10⁶ sulfur introduces donor states in gap



Janzén et al., Phys. Rev. B 29, 1907 (1984)

at high concentration states broaden into band



absorptance
$$(1 - R_{int} - T_{int})$$



Asenbaum, Vienna

absorptance
$$(1 - R_{int} - T_{int})$$



Asenbaum, Vienna

should have shallow junction below surface



excellent rectification (after annealing)



isolate surface layer for Hall measurements

device layer

buried oxide

silicon substrate
isolate surface layer for Hall measurements



device layer buried oxide

silicon substrate

isolate surface layer for Hall measurements

laser doped region

buried oxide

silicon substrate

isolate surface layer for Hall measurements



isolate surface layer for Hall measurements





























impurity (donor) band centered at 310 meV



majority carrier mobility



Caughey et al., Proc. IEEE 55, 2192 (1967)

majority carrier mobility



Caughey et al., Proc. IEEE 55, 2192 (1967)











What causes gain?

- impact excitation (avalanching)
- carrier lifetime >> transit time (photoconductive gain)
- some other mechanism



"pl junction"



formation of partially depleted region



formation of partially depleted region



apply backward bias...



...incident photon generates electron-hole pair...



...incident photon generates electron-hole pair...



... carriers accelerate away from each other...



...hole is trapped



meanwhile electron exits sample...



...and source provides new electron
Optical hyperdoping

Things to keep in mind

- can turn absorption into carrier generation
- very high responsivity in VIS and IR
- phenomenal photoconductive gain

Optical hyperdoping



SiOnyx



Materials processing with femtosecond lasers:

• new physics

new processes

new applications



What is different about this doping process?



Compare femtosecond laser doping to:

- inclusion during growth
- thermal diffusion
- ion implantation



Army Research Office DARPA Department of Energy NDSEG National Science Foundation

Funding:

for more information:

http://mazur-www.harvard.edu



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